

N-Channel Enhancement Mode Power MOSFET

Description

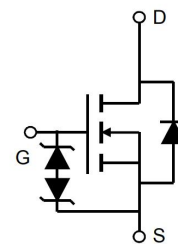
The G7K2N20HE uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

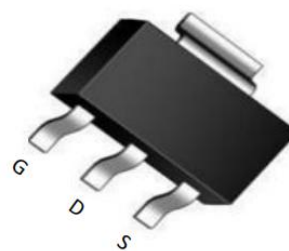
- V_{DS} 200V
- I_D (at $V_{GS} = 10V$) 2A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 0.70 Ω
- $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 0.72 Ω
- 100% Avalanche Tested
- RoHS Compliant
- ESD (HBM)>4KV

Application

- Power switch
- DC/DC converters



Schematic diagram



SOT-223

Ordering Information

Device	Package	Marking	Packaging
G7K2N20HE	SOT-223	G7K2N20	2500psc/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	200	V
Continuous Drain Current	I_D	2	A
Pulsed Drain Current (note1)	I_{DM}	8	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	1.8	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	70	$^\circ\text{C/W}$

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	200	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 200V, V _{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±30	uA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.8	2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 1A	--	0.55	0.70	Ω
		V _{GS} = 4.5V, I _D = 1A	--	0.57	0.72	
Forward Transconductance	g _{FS}	V _{GS} = 5V, I _D = 1A	--	0.94	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 100V, f = 1.0MHz	--	568	--	pF
Output Capacitance	C _{oss}		--	13	--	
Reverse Transfer Capacitance	C _{rss}		--	10	--	
Total Gate Charge	Q _g	V _{DD} = 100V, I _D = 1A, V _{GS} = 10V	--	10.8	--	nC
Gate-Source Charge	Q _{gs}		--	1.7	--	
Gate-Drain Charge	Q _{gd}		--	3.1	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 100V, I _D = 1A, R _G = 10Ω	--	10.7	--	ns
Turn-on Rise Time	t _r		--	7.3	--	
Turn-off Delay Time	t _{d(off)}		--	18.2	--	
Turn-off Fall Time	t _f		--	11.9	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	2	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 1A, V _{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Q _{rr}	I _F = 1A, V _{GS} = 0V di/dt=100A/us	--	357	--	nC
Reverse Recovery Time	T _{rr}		--	125	--	ns

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

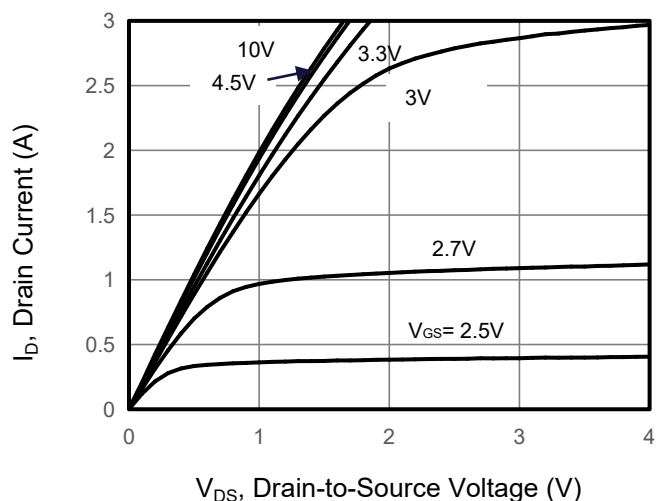


Figure 2. Transfer Characteristics

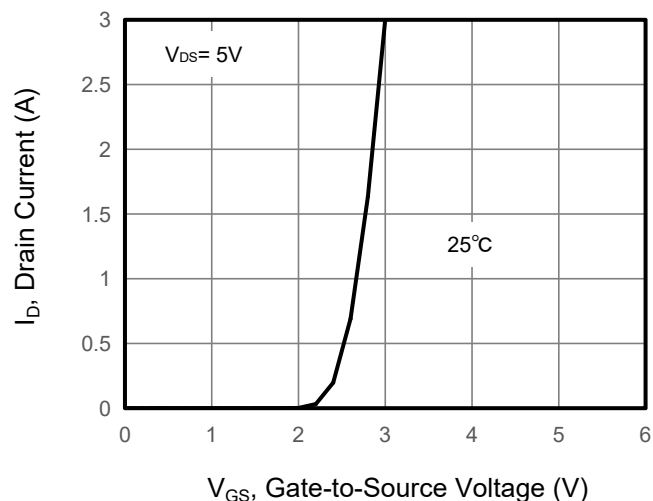


Figure 3. Drain Source On Resistance

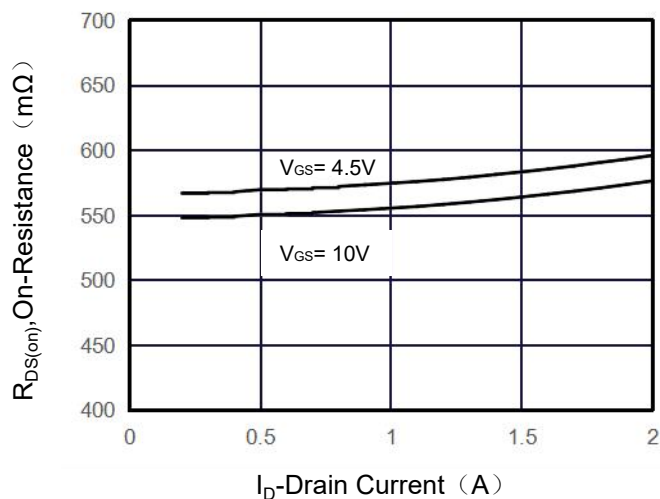


Figure 4. Gate Charge

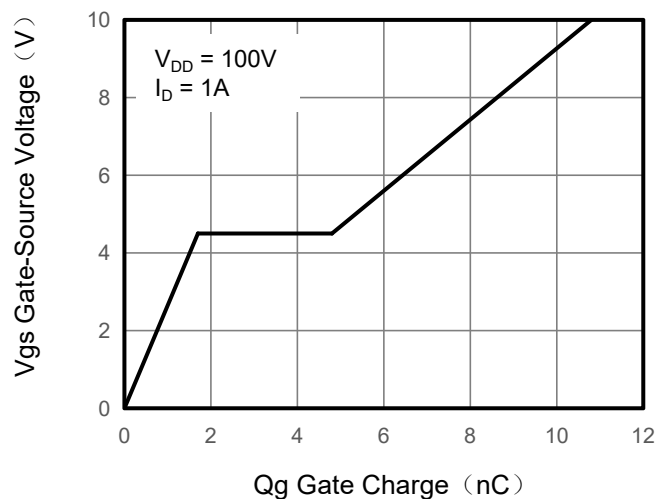


Figure 5. Capacitance

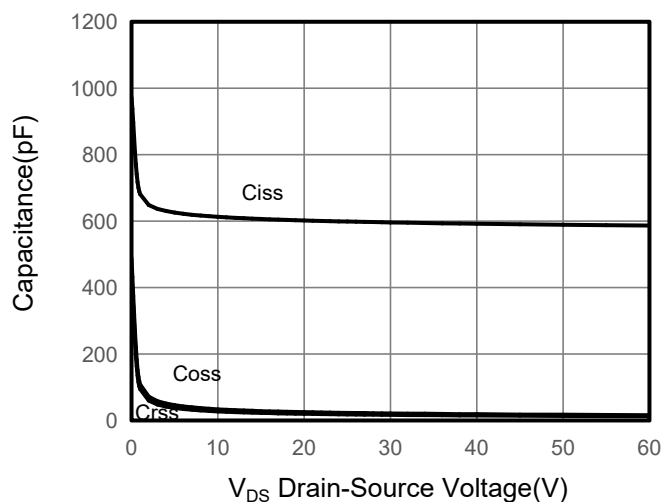
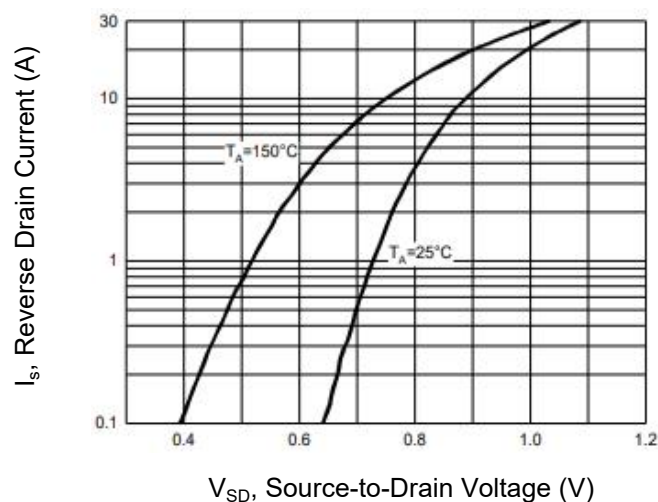


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

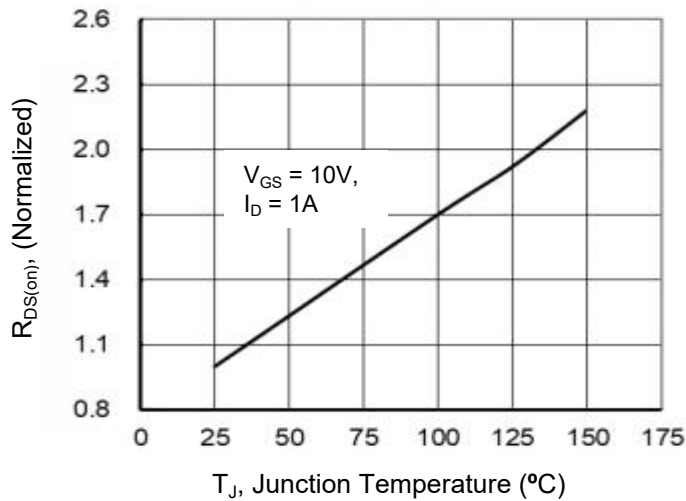


Figure 8. Safe Operation Area

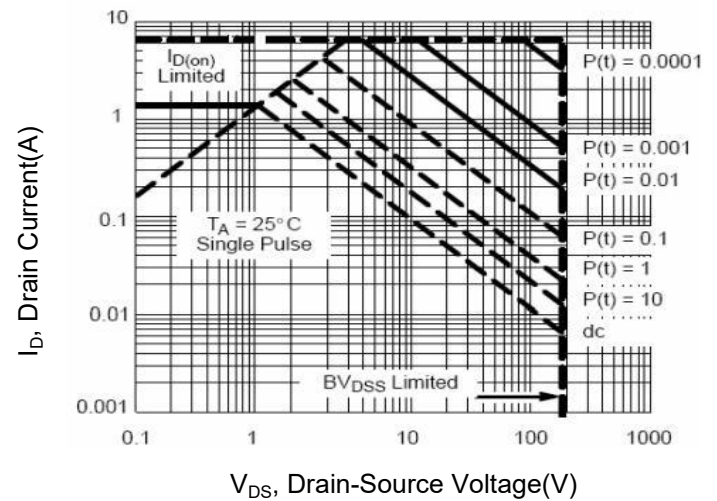
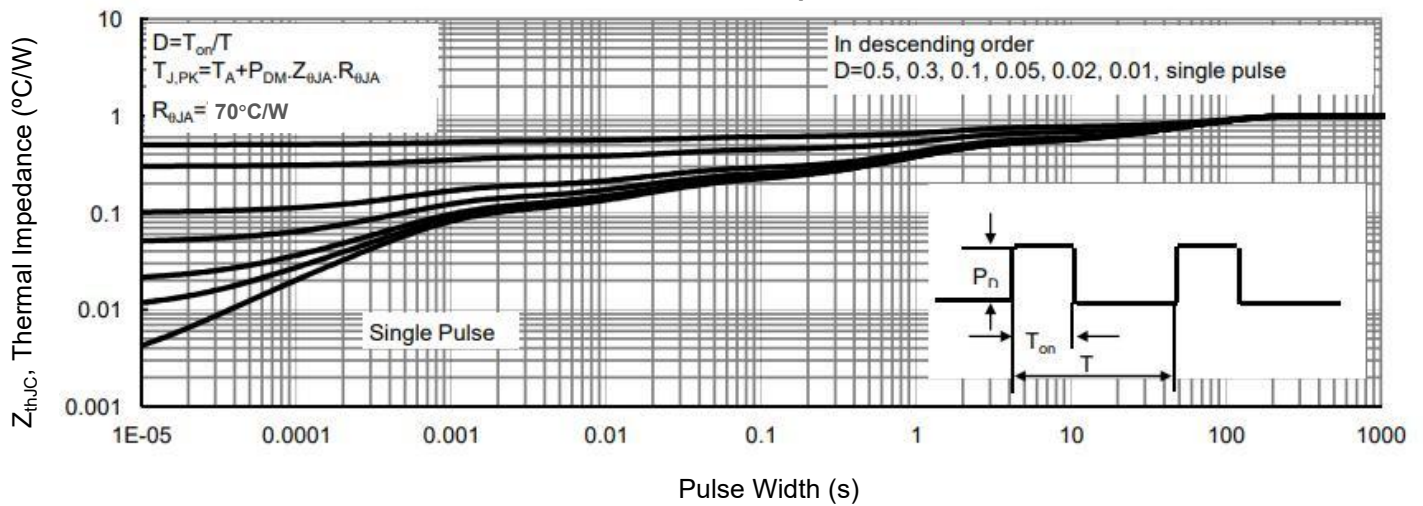
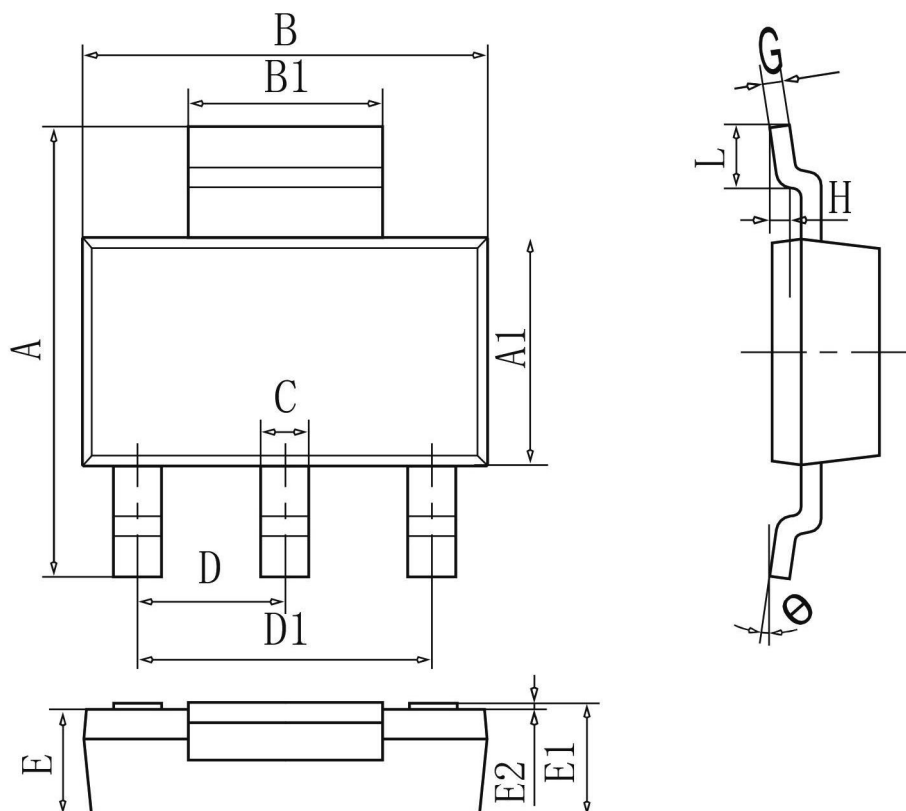


Figure 9. Normalized Maximum Transient Thermal Impedance



SOT-223 Package Information



DIM	MIN	NOM	MAX
A	6.80	7.00	7.20
A1	3.30	3.50	3.70
B	6.40	6.60	6.80
B1	2.96	3.00	3.10
C	0.66	0.70	0.80
D	2.25	2.30	2.35
D1	4.60REF		
E	1.50	1.60	1.70
E1	1.65REF		
E2	0.02	0.06	0.10
G	0.255	0.305	0.355
H	0.25GAUGR		
L	0.90	—	—
θ	0°	—	10°
All Dimensions in mm			